

version, except that marked up versions are not being supplied for any added claim or canceled claim.

- SEC 101
1. (Once amended) A semiconductor processing method, comprising:
- forming a layer of material comprising oxygen, as initially deposited, over a semiconductive wafer substrate;
- exposing some portions of the layer to energy while leaving other portions unexposed, the exposing altering physical properties of the exposed portions of material relative to the unexposed portions of material;
- after the exposing, subjecting the exposed and unexposed portions of the layer to common conditions, the common conditions being effective to remove the material and comprising a rate of removal that is influenced by the altered physical properties of the layer, the common conditions removing either the exposed or unexposed portions faster than the other of the exposed and unexposed portions; and
- after the selective removal of the exposed or unexposed portions, and while the other of the exposed and unexposed portions remains over the substrate, cutting the wafer into separated die.
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